Complementary Silicon Power Plastic Transistors

These devices are designed for low voltage, low-power, high-gain audio amplifier applications.

Features

- High DC Current Gain
- Low Collector-Emitter Saturation Voltage
- High Current-Gain Bandwidth Product
- Annular Construction for Low Leakage
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|--------------|------------|
| Collector-Emitter Voltage | V _{CEO} | 40 | Vdc |
| Collector-Base Voltage | V _{CB} | 25 | Vdc |
| Emitter-Base Voltage | V _{EB} | 8.0 | Vdc |
| Collector Current – Continuous | I _C | 5.0 | Adc |
| Collector Current – Peak | I _{CM} | 10 | Adc |
| Base Current | Ι _Β | 1.0 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | P _D | 15 0.12 | W mW/°C |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | P _D | 1.5 0.012 | W mW/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

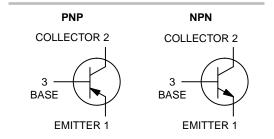
| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 8.34 | °C/W |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 83.4 | °C/W |



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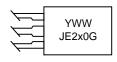
http://onsemi.com

5.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 25 VOLTS, 15 WATTS





MARKING DIAGRAM



ORDERING INFORMATION

| Device | Package | Shipping |
|----------|---------------------|-----------------|
| MJE200G | TO-225 (Pb-Free) | 500 Units / Box |
| MJE210G | TO-225 (Pb-Free) | 500 Units / Box |
| MJE210TG | TO-225 (Pb-Free) | 500 Units / Box |

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---|-----------------------|----------------|--------------------|--------------|
| OFF CHARACTERISTICS | • | • | | |
| Collector–Emitter Sustaining Voltage (Note 1) (I _C = 10 mAdc, I _B = 0) | V _{CEO(sus)} | 25 | - | Vdc |
| Collector Cutoff Current $(V_{CB} = 40 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 40 \text{ Vdc}, I_E = 0, T_J = 125^{\circ}\text{C})$ | I _{CBO} | - - | 100 100 | nAdc μAdc |
| Emitter Cutoff Current (V _{BE} = 8.0 Vdc, I _C = 0) | I _{EBO} | - | 100 | nAdc |
| ON CHARACTERISTICS | • | | | |
| DC Current Gain (Note 1) ($I_C = 500 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 5.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) | h _{FE} | 70 45 10 | - 180 - | - |
| | V _{CE(sat)} | - - - | 0.3 0.75 1.8 | Vdc |
| Base–Emitter Saturation Voltage (Note 1) (I _C = 5.0 Adc, I _B = 1.0 Adc) | V _{BE(sat)} | - | 2.5 | Vdc |
| Base–Emitter On Voltage (Note 1) (I _C = 2.0 Adc, V _{CE} = 1.0 Vdc) | V _{BE(on)} | _ | 1.6 | Vdc |
| DYNAMIC CHARACTERISTICS | • | • | • | |
| Current–Gain – Bandwidth Product (Note 2) $(I_C = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 10 \text{ MHz})$ | f _T | 65 | _ | MHz |
| Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz) MJE200 MJE210 | C _{ob} | - - | 80 120 | pF |

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \approx 2.0%. 2. $f_T = |h_{fe}| \bullet f_{test}$.

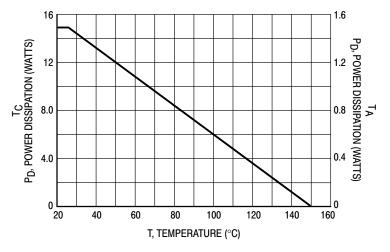
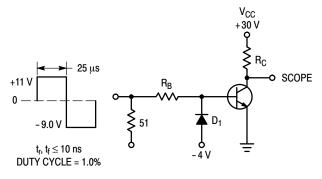


Figure 1. Power Derating



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS D1 MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE $I_B\approx 100~\text{mA}$ MSD6100 USED BELOW $I_B\approx 100~\text{mA}$

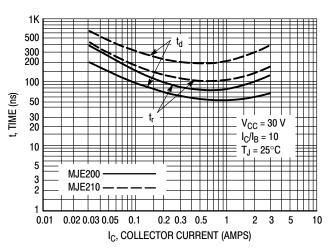
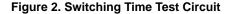


Figure 3. Turn-On Time



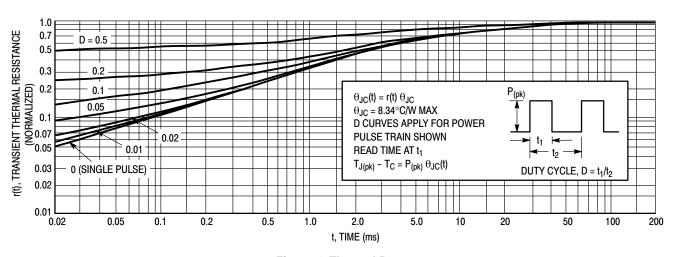


Figure 4. Thermal Response

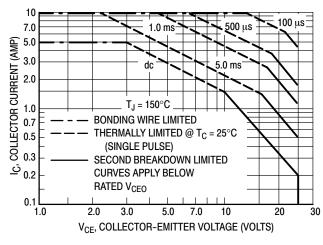
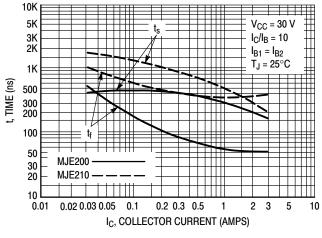


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



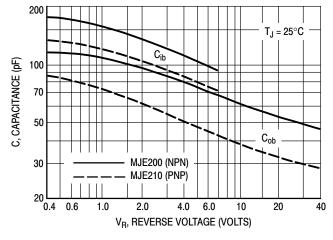
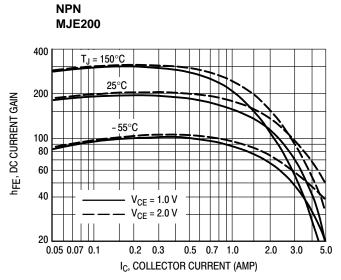


Figure 6. Turn-Off Time

Figure 7. Capacitance



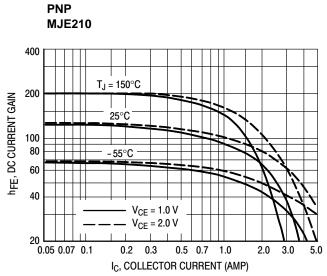
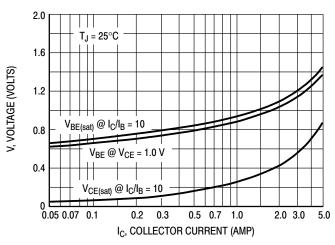


Figure 8. DC Current Gain



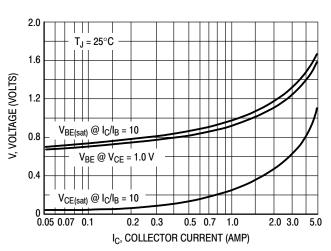


Figure 9. "On" Voltage

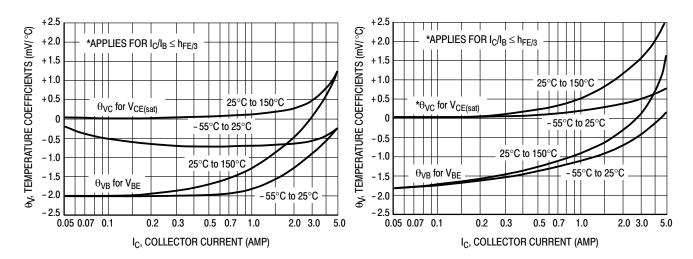
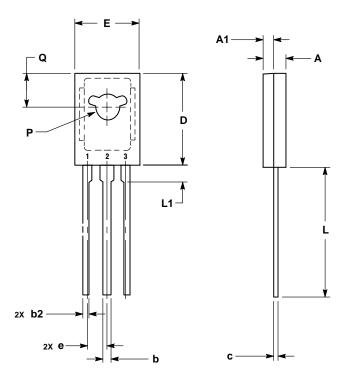


Figure 10. Temperature Coefficients

PACKAGE DIMENSIONS

TO-225 CASE 77-09 **ISSUE AB**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

| | MILLIMETERS | | |
|-----|-------------|-------|--|
| DIM | MIN | MAX | |
| Α | 2.40 | 3.00 | |
| A1 | 1.00 | 1.50 | |
| b | 0.60 | 0.90 | |
| b2 | 0.51 | 0.88 | |
| С | 0.39 | 0.63 | |
| D | 10.60 | 11.10 | |
| E | 7.40 | 7.80 | |
| е | 2.04 | 2.54 | |
| L | 14.50 | 16.63 | |
| L1 | 1.27 | 2.54 | |
| P | 2.90 | 3.30 | |
| Q | 3.80 | 4.20 | |

STYLE 1:

PIN 1 FMITTER

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